



Multifunctional Chip 多功能芯片

MKR-9296BF-4R (short form datasheet)

4-Channel Beamforming Receiver Chip

Feature:

- Freq: 92GHz~96GHz
- NF: ≤ 7 dB
- Phase shift step: $22.5^\circ@94$ GHz
- Phase control: 4-bit
- LO freq: 28GHz
- IF freq: 8-12GHz
- Power supply: 5V (130mA single channel)
3.3V (40mA)
- Control mode: 3.3V TTL
- Footprint: 2.7mm \times 2.7mm \times 0.1mm
- Made in China

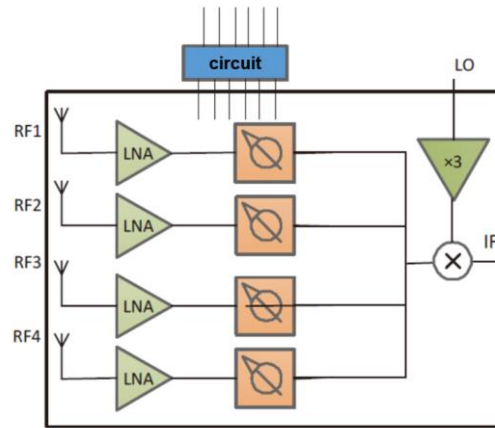
General Description

MKR-9296BF-4R is a 4-channel receiver downconverter. bare die on W Band. Each channel contains a RF input with a low noise amplifier (LNA) and a downconverter mixer with x3 LO Chain. Control of the on-chip registers is 4 bit.

Electrical Characteristics : ($T_A=+25^\circ\text{C}$)

Item	Min	Typ	Max	Unit
Freq	92		96	GHz
Small signal gain		22		dB
NF		7		dB
Input P1dB		-20		dBm
Input VSWR		2		-
Output VSWR		2		-
Current@5V		130		mA
Current@3.3V		40		mA
Phase shift resolution		5		degree

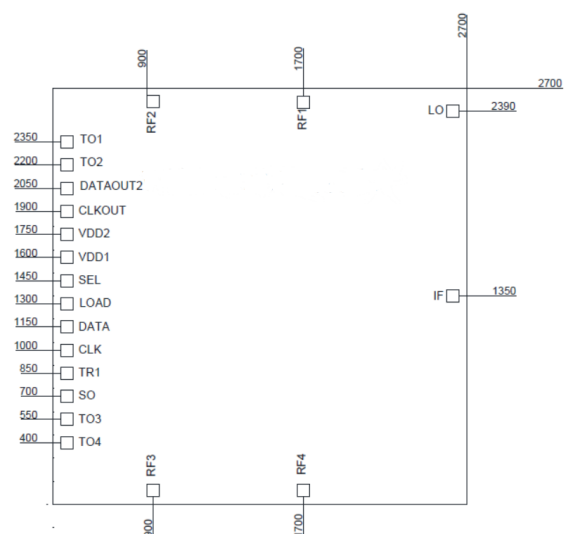
Function Diagram



Maximum Ratings:

Power supply, VDD2	5.5V
Power supply, VDD1	4V
Control voltage, CLK/DATA/LOAD/SEL/TR1	4V
Trench operating temperature, T _{ch}	150 $^\circ\text{C}$
Electro-Static discharge, ESD	200V
Storage temperature, T _{stg}	-65 $^\circ\text{C}$ ~150 $^\circ\text{C}$
Mount temperature	300 $^\circ\text{C}$ (1min, N2 protection)

Outline Drawing:

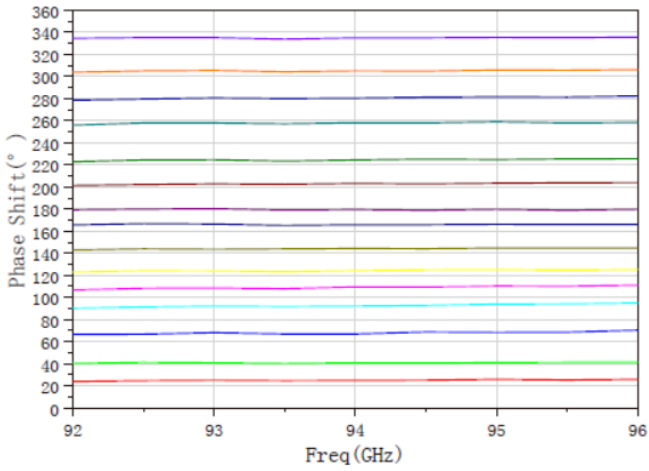


Notes: 1) All dimensions are in μm

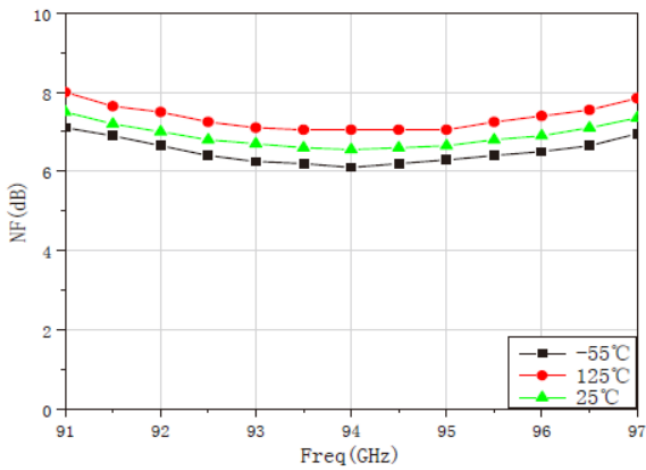
2) Substrate Thickness: 100 μm

Measured Performance (RF power: -40dBm;
LO:28GHz, LO power:10dBm, T_A=+25°C)

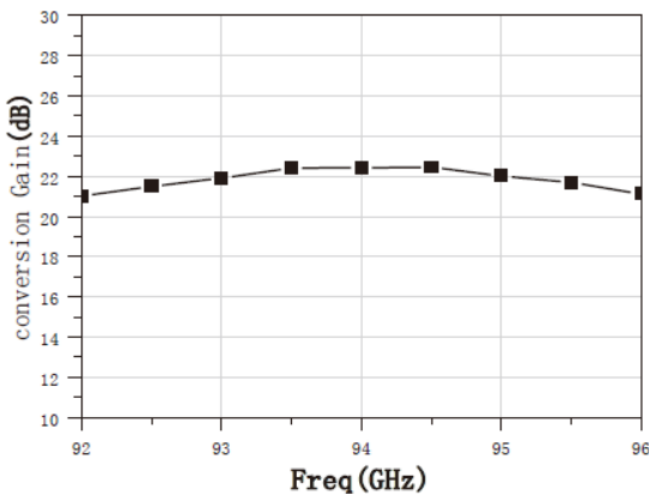
Phase-shift vs.Freq



NF vs.Freq



Conversion gain vs.Freq



Tips:

- 1) Good grounding and heat dissipation are required during use. MoCu with thermal expansion coefficient close to InP substrate ($4.6 \times 10^{-6}/K$) is recommended as carrier.
- 2) The chips are electrostatic sensitive devices. Anti-static devices should be paid attention to during use, transportation and operation, and severe collisions and drops should be avoided to avoid damaging the product.
- 3) It is recommended to install decoupling capacitors according to the recommended assembly drawing when using;
- 4) It is recommended to use the diameter of 25um gold wire as feed, input and output interconnection of chips;
- 5) This chip is a hydrogen sensitive device with a hydrogen resistance of 2000 ppm. It is recommended to control the hydrogen concentration in the sealed chamber when using.

MKR-9296BF-4T (short form datasheet)

4-Channel Beamforming Transmitter Chip

Feature:

- Freq: 92GHz~96GHz
- Psat: 14dBm
- Small signal gain: 25dB
- Phase shift step: 22.5°@94GHz
- Phase control: 4-bit
- LO freq:28GHz
- IF freq:8-12GHz
- Power supply: 5V (210mA single channel)
3.3V (30mA)
- Control mode: 3.3V TTL
- Footprint: 2.7mm×2.7mm×0.1mm
- Made in China

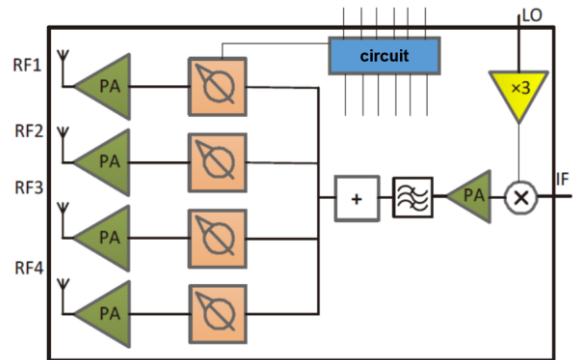
General Description

MKR9296BF-4T is a 4-channel receiver upconverter. bare die on W Band. Each channel contains a RF input with a low noise amplifier (LNA) and a downconverter mixer with x3 LO Chain. Control of the on-chip registers is 4 bit.

Electrical Characteristics : (T_A=+25°C)

Item	Min	Typ	Max	Unit
Freq	92		96	GHz
Small signal gain		25		dB
Psat		14		dBm
Input VSWR		2		-
Output VSWR		2		-
Current@5V		210		mA
Current@3.3V		30		mA
Phase shift resolution		5		degree

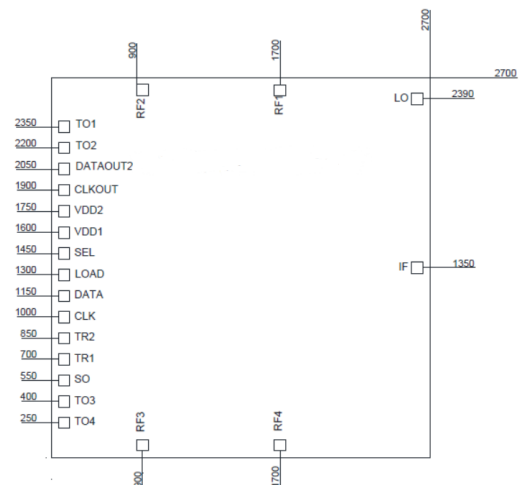
Function Diagram



Maximum Ratings:

Power supply, VDD2	5.5V
Power supply, VDD1	4V
Control voltage, CLK/DATA/LOAD/SEL/TR1	4V
Trench operating temperature, Tch	150°C
Electro-Static discharge, ESD	200V
Storage temperature, Tstg	-65°C~150°C
Mount temperature	300°C (1min, N2 protection)

Outline Drawing:



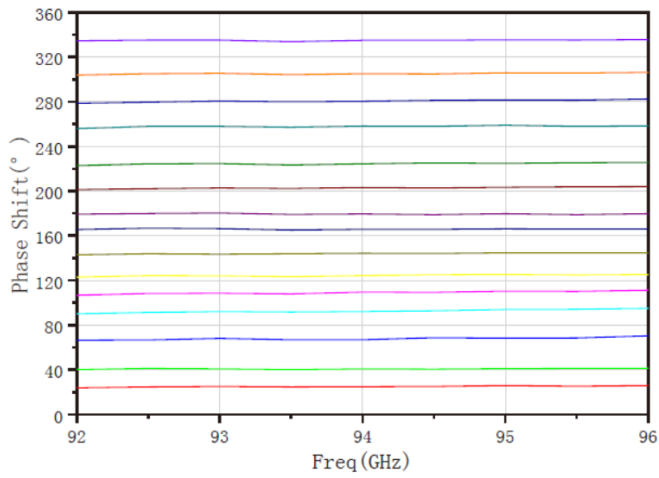
Notes: 1) All dimensions are in μm

2) Substrate Thickness:100 μm

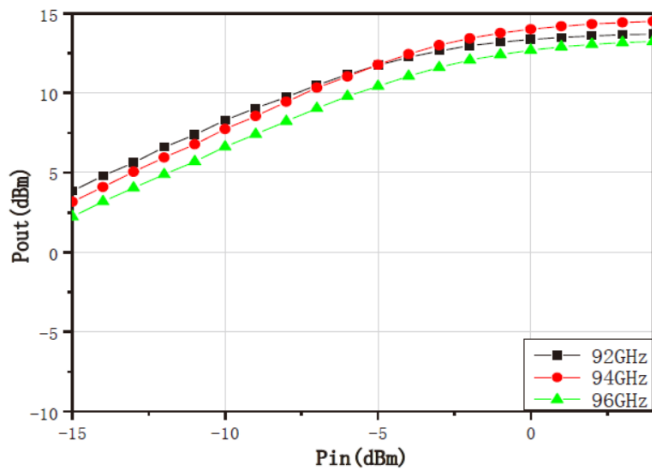
Measured Performance (LO power: 10dBm;

LO:28GHz, IF power:-9dBm, $T_A=+25^\circ\text{C}$)

Phase-shift vs.Freq



Output power vs.Pin



Tips:

- 1) Good grounding and heat dissipation are required during use. MoCu with thermal expansion coefficient close to InP substrate ($4.6 \times 10^{-6}/\text{K}$) is recommended as carrier.
- 2) The chips are electrostatic sensitive devices. Anti-static devices should be paid attention to during use, transportation and operation, and severe collisions and drops should be avoided to avoid damaging the product.
- 3) It is recommended to install decoupling capacitors according to the recommended assembly drawing when using;
- 4) It is recommended to use the diameter of 25um gold wire as feed, input and output interconnection of chips;
- 5) This chip is a hydrogen sensitive device with a hydrogen resistance of 2000 ppm. It is recommended to control the hydrogen concentration in the sealed chamber when using.

MKR-9498BF-4R (short form datasheet)

4-Channel Beamforming Receiver Chip

Feature:

- Freq: 94GHz~98GHz
- NF: 7dB
- Gain: 22dB
- Phase shift step: 11.25°@96GHz
- Phase control: 5-bit
- LO freq:20GHz
- IF freq:14-18GHz
- Power supply: 5V (130mA single channel)
3.3V (40mA)
- Control mode: 3.3V TTL
- Footprint: 2.7mm×3.9mm×0.1mm
- Made in China

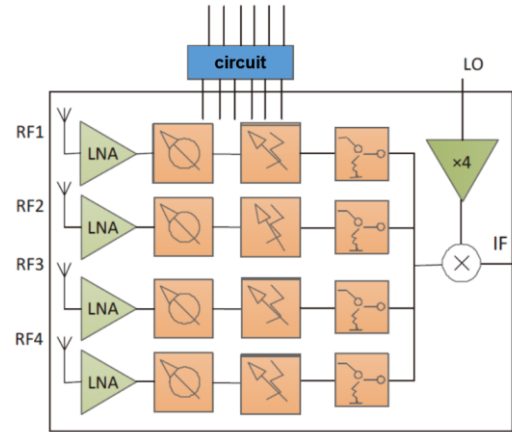
General Description

MKR-9498BF-4R is a 4-channel receiver downconverter. bare die on W Band. Each channel contains a RF input with a low noise amplifier (LNA) and a downconverter mixer with x4 LO Chain. Control of the on-chip registers is 4 bit.

Electrical Characteristics : (T_A=+25°C)

Item	Min	Typ	Max	Unit
Freq	94		98	GHz
Small signal gain		22		dB
NF			7	dB
Input P1dB		-20		dBm
Input VSWR		2		-
Output VSWR		2		-
Current@5V		130		mA
Current@3.3V		40		mA
Phase shift resolution		3		degree

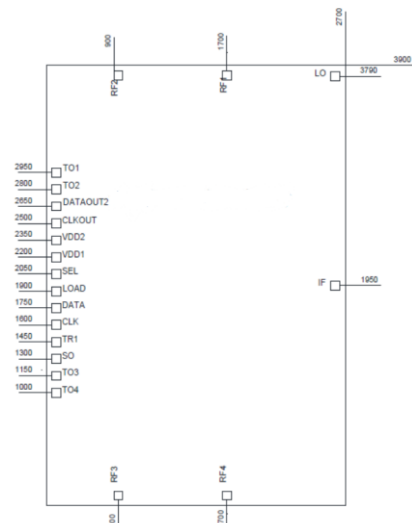
Function Diagram



Maximum Ratings:

Power supply, VDD2	5.5V
Power supply, VDD1	4V
Control voltage, CLK/DATA/LOAD/SEL/TR1	4V
Trench operating temperature, T _{ch}	150°C
Electro-Static discharge, ESD	200V
Storage temperature, T _{stg}	-65°C~150°C
Mount temperature	300°C (1min, N2 protection)

Outline Drawing:



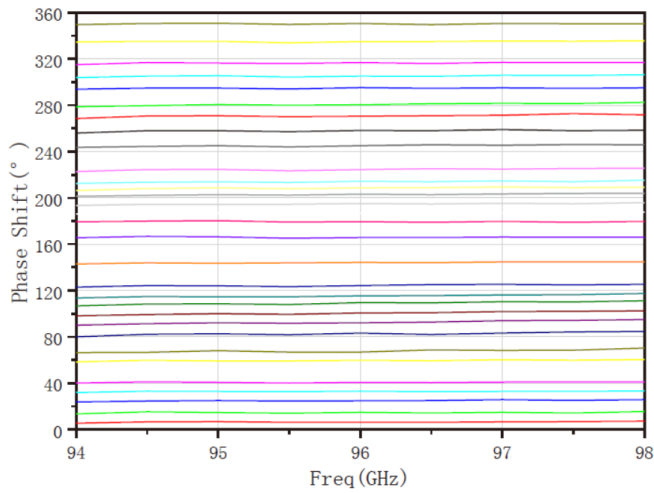
Notes: 1) All dimensions are in μm

2) Substrate Thickness:100 μm

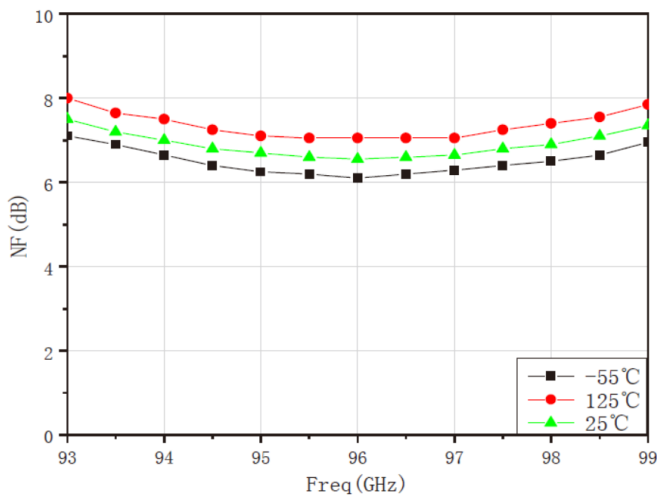


Measured Performance (RF power: -40dBm;
LO:20GHz, LO power:0dBm, T_A=+25°C)

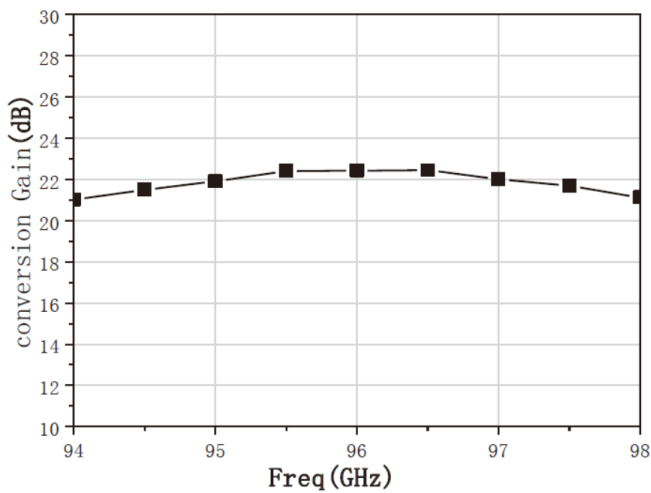
Phase-shift vs.Freq



NF vs.Freq



Conversion gain vs.Freq



Tips:

- 1) Good grounding and heat dissipation are required during use. MoCu with thermal expansion coefficient close to InP substrate ($4.6 \times 10^{-6}/K$) is recommended as carrier.
- 2) The chips are electrostatic sensitive devices. Anti-static devices should be paid attention to during use, transportation and operation, and severe collisions and drops should be avoided to avoid damaging the product.
- 3) It is recommended to install decoupling capacitors according to the recommended assembly drawing when using;
- 4) It is recommended to use the diameter of 25um gold wire as feed, input and output interconnection of chips;
- 5) This chip is a hydrogen sensitive device with a hydrogen resistance of 2000 ppm. It is recommended to control the hydrogen concentration in the sealed chamber when using.

MKR-9498BF-4T (short form datasheet)

4-Channel Beamforming Transmitter Chip

Feature:

- Freq: 94GHz~98GHz
- Psat: 14dBm
- Small signal gain: 25dB
- Phase shift step: 11.25°@96GHz
- Phase shift resolution: 3°
- Phase control: 5-bit
- LO freq:20GHz
- IF freq:14-18GHz
- Power supply: 5V (210mA single channel)
3.3V (30mA)
- Control mode: 3.3V TTL
- Footprint: 2.7mm×3.3mm×0.1mm
- Made in China

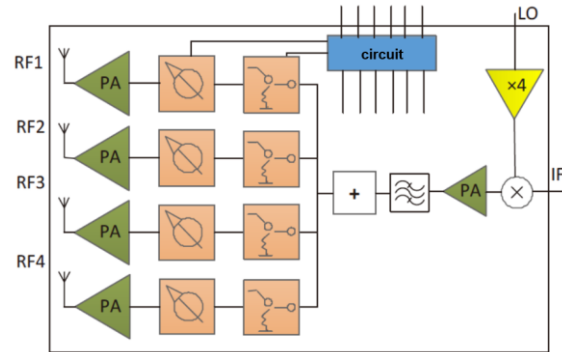
General Description

MKR-9498BF-4T is a 4-channel receiver upconverter bare die on W Band. Each channel contains a RF input with a low noise amplifier (LNA) and a downconverter mixer with x4 LO Chain. Control of the on-chip registers is 4 bit.

Electrical Characteristics : (T_A=+25°C)

Item	Min	Typ	Max	Unit
Freq	94		98	GHz
Small signal gain		25		dB
Psat		14		dBm
Input VSWR		2		-
Current@5V		210		mA
Current@3.3V		30		mA
Phase shift resolution		3		degree

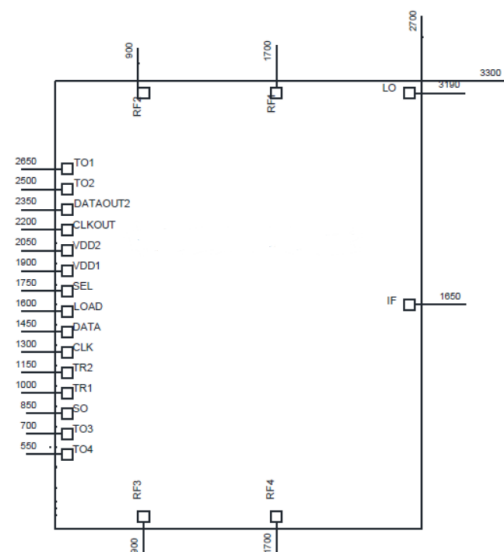
Function Diagram



Maximum Ratings:

Power supply, VDD2	5.5V
Power supply, VDD1	4V
Control voltage, CLK/DATA/LOAD/SEL/TR1	4V
Trench operating temperature, Tch	150°C
Electro-Static discharge, ESD	200V
Storage temperature, Tstg	-65°C~150°C
Mount temperature	300°C (1min, N2 protection)

Outline Drawing:

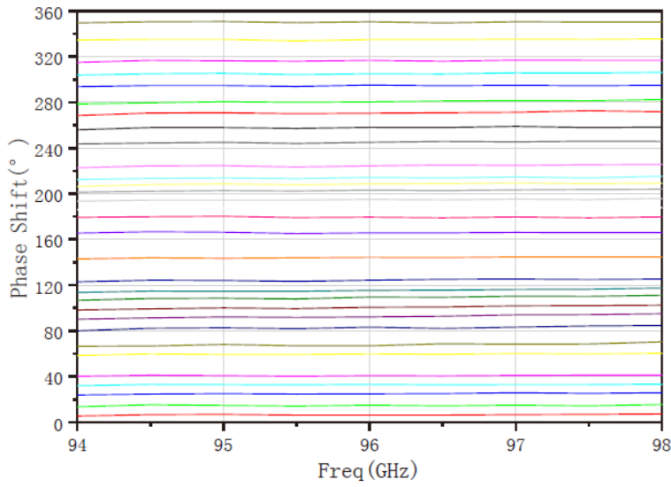


Notes: 1) All dimensions are in µm

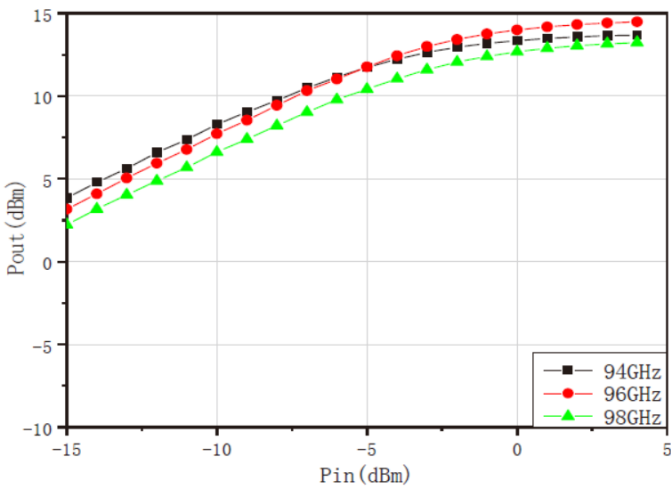
2) Substrate Thickness:100µm

**Measured Performance (LO power: 0dBm; LO:20GHz,
IF power:-15dBm, $T_A=+25^\circ\text{C}$)**

Phase-shift vs.Freq



Output power vs.Pin



Tips:

- 1) Good grounding and heat dissipation are required during use. MoCu with thermal expansion coefficient close to InP substrate ($4.6 \times 10^{-6}/\text{K}$) is recommended as carrier.
- 2) The chips are electrostatic sensitive devices. Anti-static devices should be paid attention to during use, transportation and operation, and severe collisions and drops should be avoided to avoid damaging the product.
- 3) It is recommended to install decoupling capacitors according to the recommended assembly drawing when using;
- 4) It is recommended to use the diameter of 25um gold wire as feed, input and output interconnection of chips;
- 5) This chip is a hydrogen sensitive device with a hydrogen resistance of 2000 ppm. It is recommended to control the hydrogen concentration in the sealed chamber when using.

MKR-90100UP3 (short form datasheet)

Up Converter Multifunction Chip

Feature:

- RF freq: 90GHz~100GHz
- LO: 28GHz
- LO power: 10dBm
- IF: 6GHz~16GHz
- Conversion gain:-1dB
- DC: 5V/30mA
- Footprint: 1.05mm×0.7mm×0.1mm
- Made in China

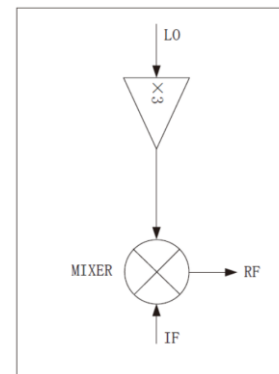
General Description

MKR-90100UP3 is a W band upconverter MMIC. Each chip contains an upconverter mixer with x3 LO Chain. All chips are RF measured, can be used for radar, communications etc. transceiver systems.

Electrical Characteristics : ($T_A=+25^{\circ}\text{C}$)

Item	Min	Typ	Max	Unit
RF Freq	90		100	GHz
LO		28		GHz
IF	6		16	GHz
Pout		-13		dBm
Conversion gain		-1		dB
3LO-RF Isolation		32		dB
Dynamic current		30		mA

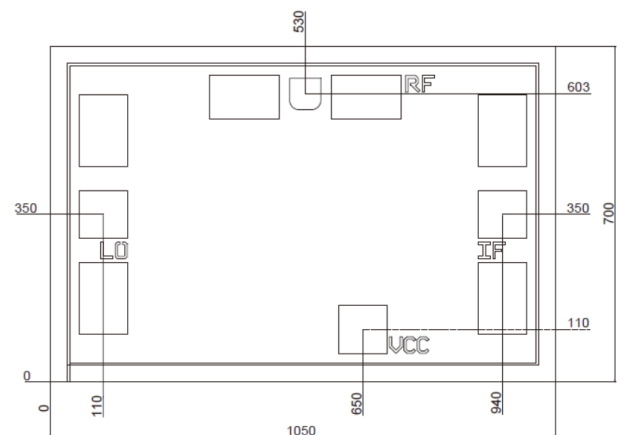
Function Diagram



Maximum Ratings:

Power supply, Vcc	5.5V
LO power	15dBm
IF power	10dBm
Trench operating temperature, Tch	175 °C
Storage temperature, Tstg	-65 °C~150 °C
Mount temperature	310 °C (1min, N2 protection)

Outline Drawing:

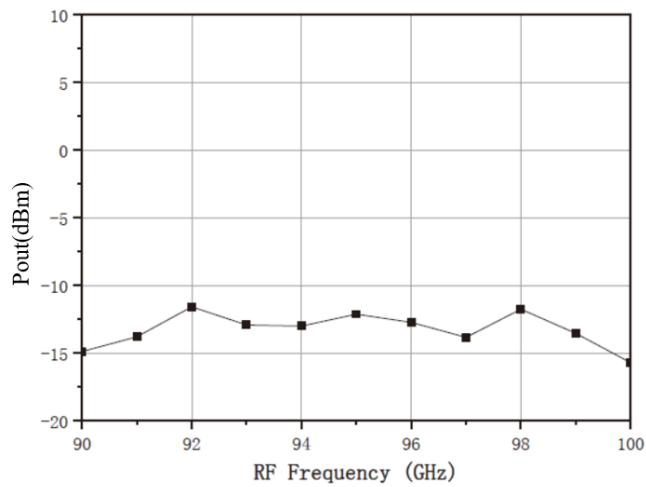


Notes: 1) All dimensions are in μm

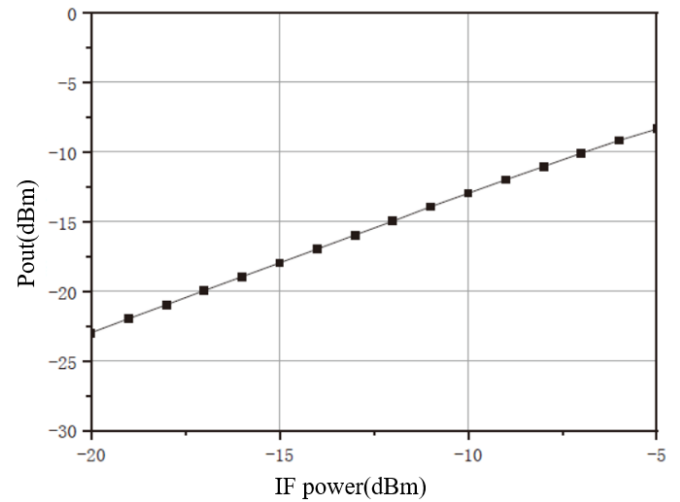
2) Substrate Thickness:100 μm

Measured Performance (Vcc=5V, LO Freq=28GHz,
LO Power=10dBm, IF Power=-12dBm, T_A=+25°C)

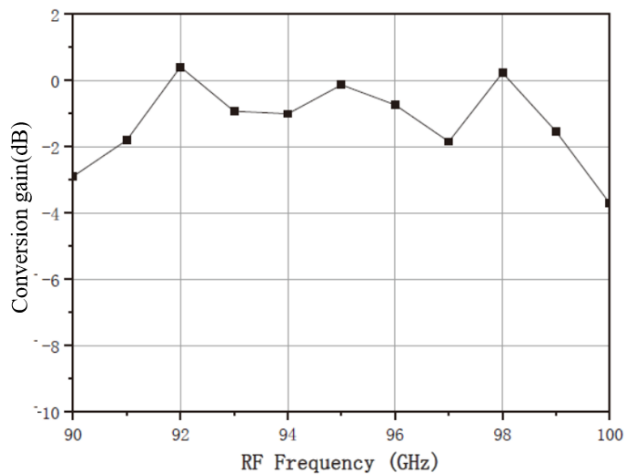
Output power vs.Freq



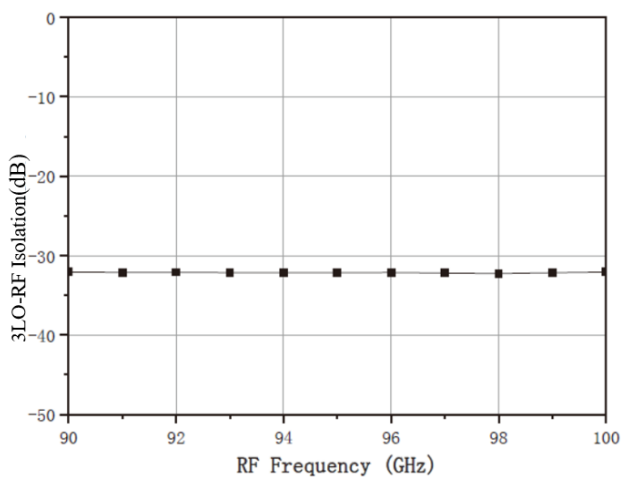
RF Output power vs.IF input power@Freq_IF=10GHz



Conversion gain vs. Freq



3LO-RF Isolation vs. Freq



Tips:

- 1) Good grounding and heat dissipation are required during use. MoCu with thermal expansion coefficient close to InP substrate ($4.6 \times 10^{-6}/K$) is recommended as carrier.
- 2) The chips are electrostatic sensitive devices. Anti-static devices should be paid attention to during use, transportation and operation, and severe collisions and drops should be avoided to avoid damaging the product.
- 3) It is recommended to install decoupling capacitors according to the recommended assembly drawing when using;
- 4) It is recommended to use the diameter of 25um gold wire as feed, input and output interconnection of chips;
- 5) This chip is a hydrogen sensitive device with a hydrogen resistance of 2000 ppm. It is recommended to control the hydrogen concentration in the sealed chamber when using.

MKR-90100DW3 (short form datasheet)

Down Converter Multifunction Chip

Feature:

- RF freq: 90GHz~100GHz
- LO: 28GHz
- LO power: 10dBm
- IF: 6GHz~16GHz
- Conversion gain:3dB
- DC: 5V/30mA
- Footprint: 1.05mm×0.7mm×0.1mm
- Made in China

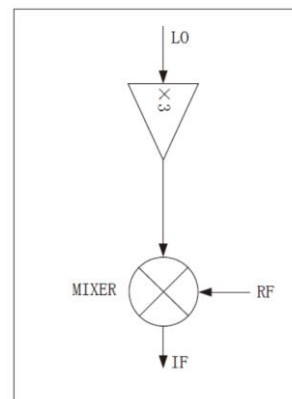
General Description

MKR-90100DW3 is a W band downconverter MMIC. Each chip contains a downconverter mixer with x3 LO Chain. All chips are RF measured, can be used for radar, communications etc. transceiver systems.

Electrical Characteristics : ($T_A=+25^{\circ}\text{C}$)

Item	Min	Typ	Max	Unit
RF Freq	90		100	GHz
LO		28		GHz
IF	6		16	GHz
IF Pout		-17		dBm
Conversion gain		3		dB
LO-RF Isolation		63		dB
Dynamic current		30		mA

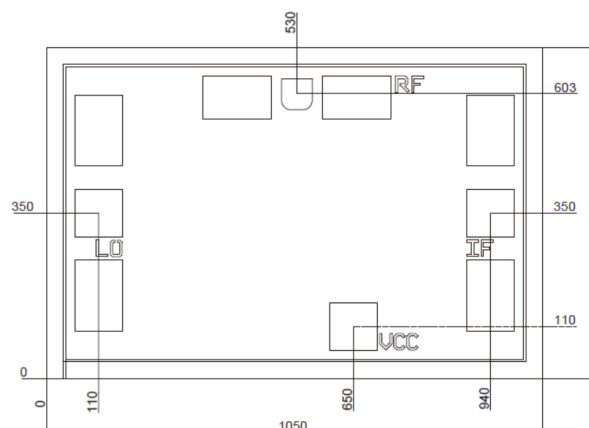
Function Diagram



Maximum Ratings:

Power supply, Vcc	6V
LO power	15dBm
RF power	10dBm
Trench operating temperature, Tch	175 $^{\circ}\text{C}$
Storage temperature, Tstg	-65 $^{\circ}\text{C}$ ~150 $^{\circ}\text{C}$
Mount temperature	310 $^{\circ}\text{C}$ (1min, N2 protection)

Outline Drawing:

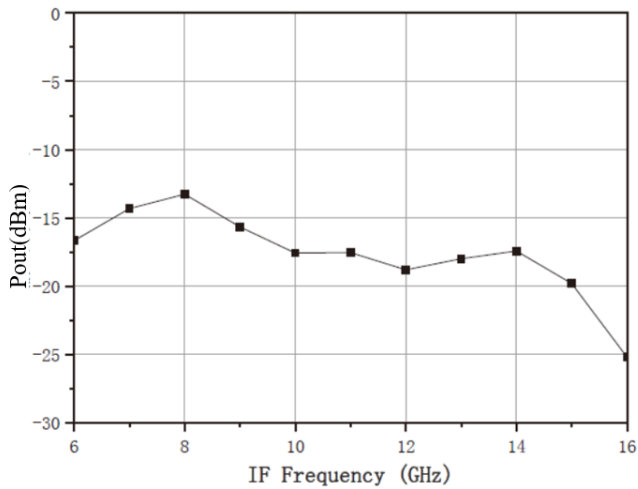


Notes: 1) All dimensions are in μm

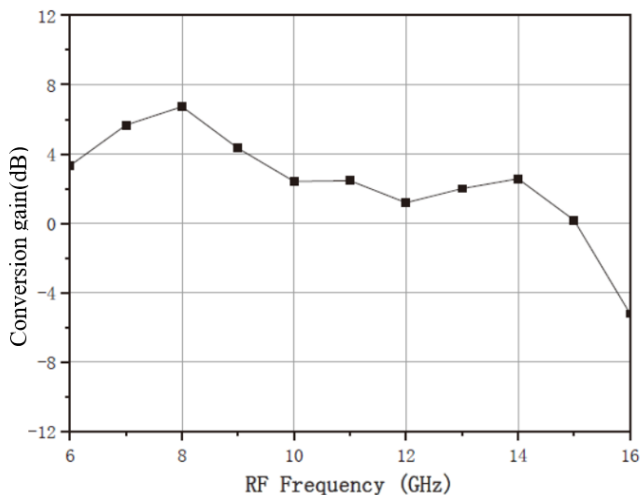
2) Substrate Thickness:100 μm

Measured Performance ($V_{cc}=5V$, LO Freq=28GHz,
LO Power=10dBm, RF Power=-20dBm, $T_A=+25^\circ C$)

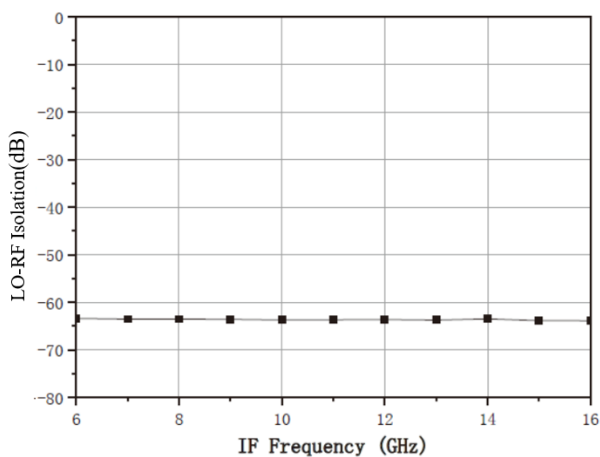
Output power vs.Freq



Conversion gain vs. Freq



LO-RF Isolation vs. Freq



Tips:

- 1) Good grounding and heat dissipation are required during use. MoCu with thermal expansion coefficient close to InP substrate ($4.6 \times 10^{-6}/K$) is recommended as carrier.
- 2) The chips are electrostatic sensitive devices. Anti-static devices should be paid attention to during use, transportation and operation, and severe collisions and drops should be avoided to avoid damaging the product.
- 3) It is recommended to install decoupling capacitors according to the recommended assembly drawing when using;
- 4) It is recommended to use the diameter of 25um gold wire as feed, input and output interconnection of chips;
- 5) This chip is a hydrogen sensitive device with a hydrogen resistance of 2000 ppm. It is recommended to control the hydrogen concentration in the sealed chamber when using.

MKR-9498DW4 (short form datasheet)

Down Converter Multifunction Chip

Feature:

- RF freq: 94GHz~98GHz
- LO: 20GHz
- LO power: 3dBm
- IF: 14GHz~18GHz
- Conversion gain:-2dB
- DC: 3.3V/36mA
- Footprint: 0.7mm×1.35mm×0.1mm
- Made in China

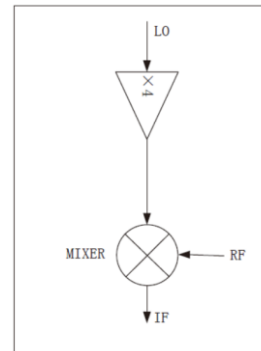
General Description

MKR-9498DW4 is a W band downconverter MMIC. Each chip contains a downconverter mixer with x4 LO Chain. All chips are RF measured, can be used for radar, communications etc. transceiver systems.

Electrical Characteristics : ($T_A=+25^{\circ}\text{C}$)

Item	Min	Typ	Max	Unit
RF Freq	94		98	GHz
LO		20		GHz
IF	14		18	GHz
IF Pout		-17		dBm
Conversion gain		-2		dB
LO-RF Isolation		52		dB
Output P1dB		3		dBm
Dynamic current		36		mA

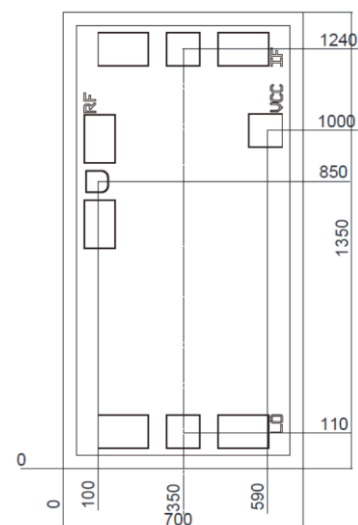
Function Diagram



Maximum Ratings:

Power supply, Vcc	4V
LO power	15dBm
RF power	10dBm
Trench operating temperature, Tch	175 °C
Storage temperature, Tstg	-65 °C~150 °C
Mount temperature	310 °C (1min, N2 protection)

Outline Drawing:

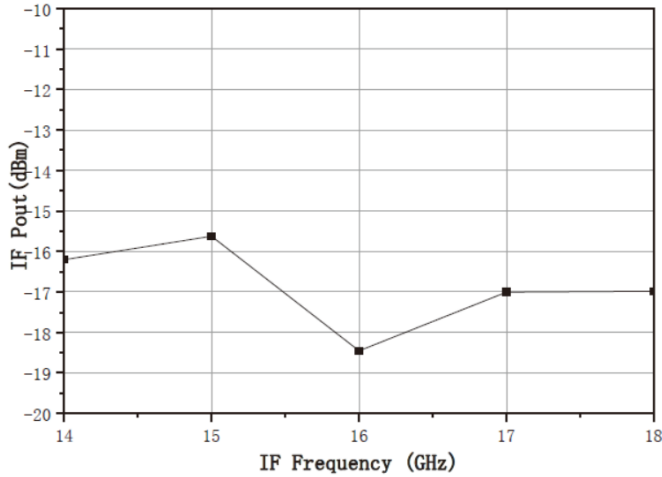


Notes: 1) All dimensions are in μm

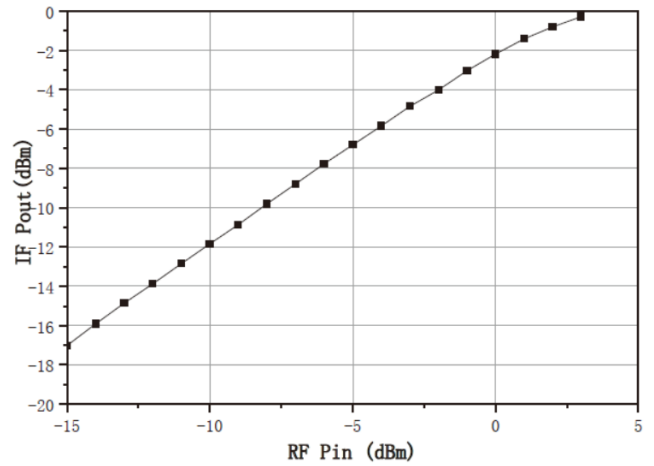
2) Substrate Thickness:100 μm

**Measured Performance (Vcc=3.3V, LO Freq=20GHz,
LO Power=3dBm, RF Power=-15dBm, T_A=+25°C)**

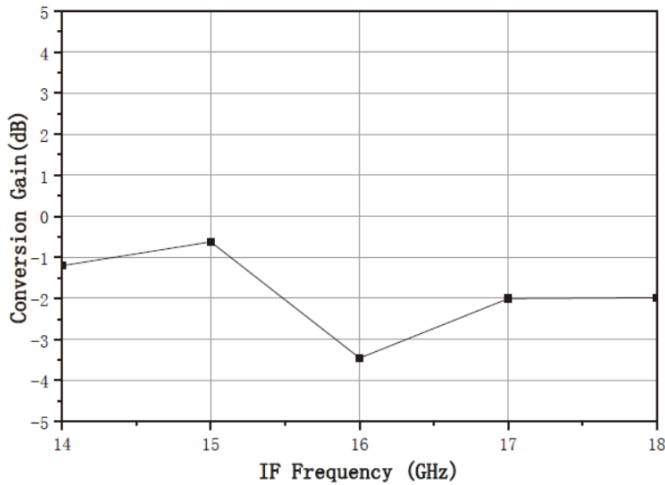
IF Output power vs.Freq



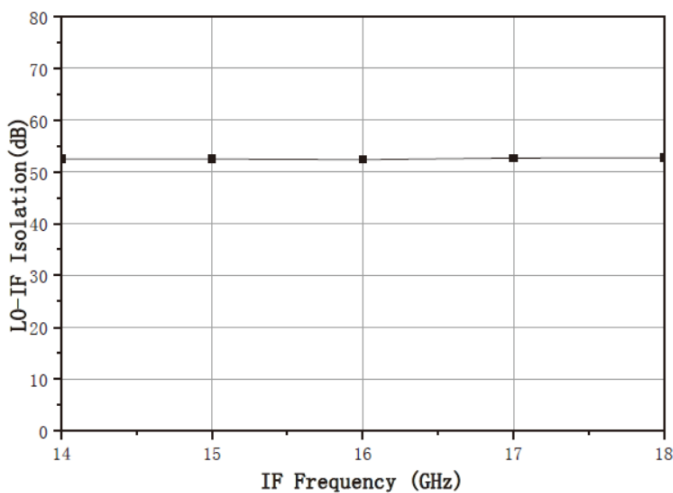
IF Output power vs.RF input power@ Freq_IF =17GHz



Conversion gain vs. Freq



LO-RF Isolation vs. Freq



Tips:

- 1) Good grounding and heat dissipation are required during use. MoCu with thermal expansion coefficient close to InP substrate ($4.6 \times 10^{-6}/K$) is recommended as carrier.
- 2) The chips are electrostatic sensitive devices. Anti-static devices should be paid attention to during use, transportation and operation, and severe collisions and drops should be avoided to avoid damaging the product.
- 3) It is recommended to install decoupling capacitors according to the recommended assembly drawing when using;
- 4) It is recommended to use the diameter of 25um gold wire as feed, input and output interconnection of chips;
- 5) This chip is a hydrogen sensitive device with a hydrogen resistance of 2000 ppm. It is recommended to control the hydrogen concentration in the sealed chamber when using.

MKR-92100UP4 (short form datasheet)

Up Converter Multifunction Chip

Feature:

- RF freq: 92GHz~100GHz
- LO: 20GHz
- LO power: 3dBm
- IF: 12GHz~20GHz
- Conversion gain:-1dB
- DC: 3.3V/45mA
- Footprint: 0.7mm×1.35mm×0.1mm
- Made in China

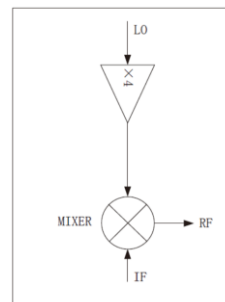
General Description

MKR-92100UP4 is a W band upconverter MMIC. Each chip contains an upconverter mixer with x4 LO Chain. All chips are RF measured, can be used for radar, communications etc. transceiver systems.

Electrical Characteristics : ($T_A=+25^{\circ}\text{C}$)

Item	Min	Typ	Max	Unit
RF Freq	92		100	GHz
LO		20		GHz
IF	12		20	GHz
Pout		-11		dBm
Conversion gain		-1		dB
4LO-RF Isolation		25		dB
Output P1dB		-1		dBm
Dynamic current		45		mA

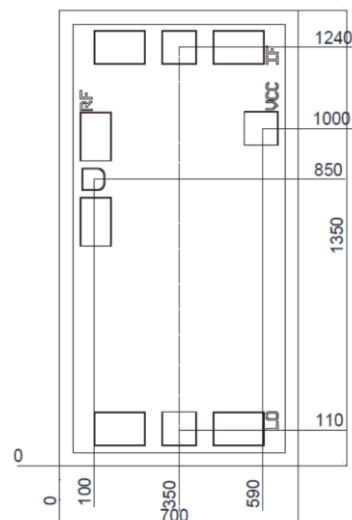
Function Diagram



Maximum Ratings:

Power supply, Vcc	4V
LO power	15dBm
IF power	15dBm
Trench operating temperature, Tch	175°C
Storage temperature, Tstg	-65°C~150°C
Mount temperature	310°C (1min, N2 protection)

Outline Drawing:

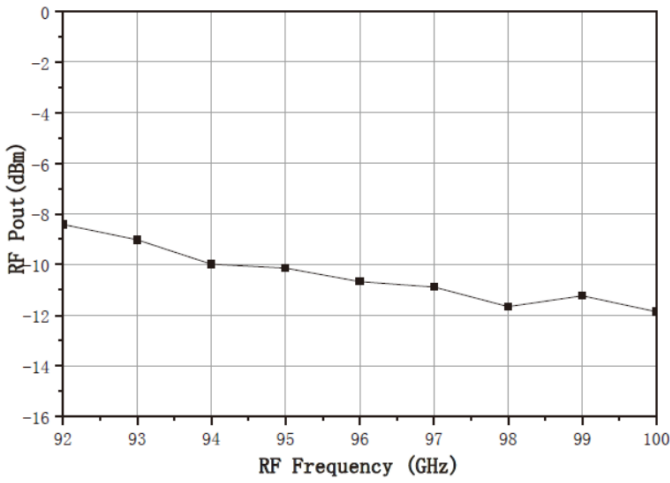


Notes: 1) All dimensions are in μm

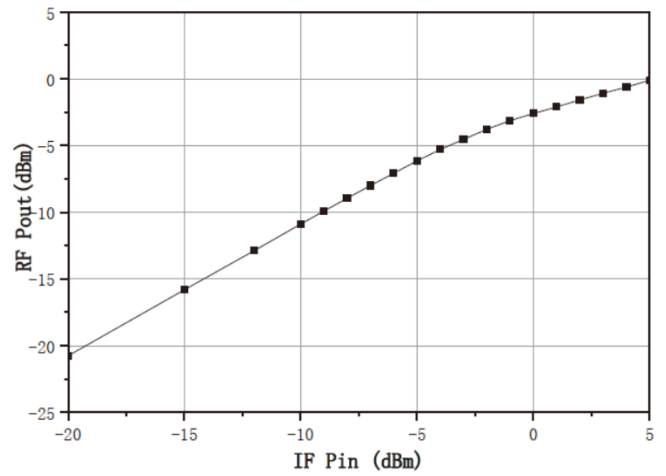
2) Substrate Thickness:100 μm

Measured Performance (Vcc=3.3V, LO Freq=20GHz,
LO Power=3dBm, IF Power=-10dBm, T_A=+25°C)

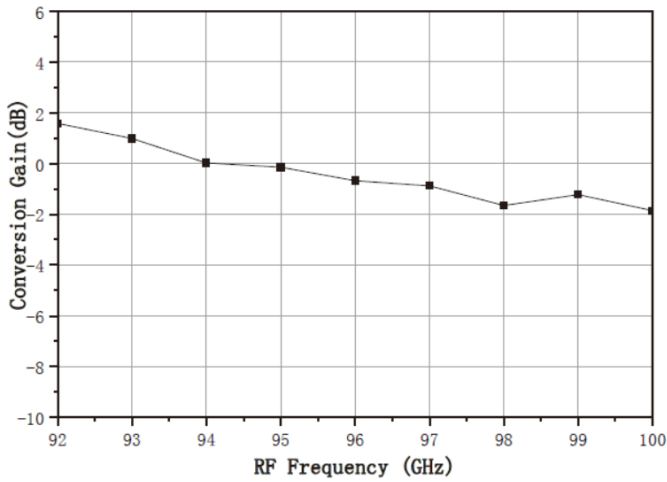
Output power vs.Freq



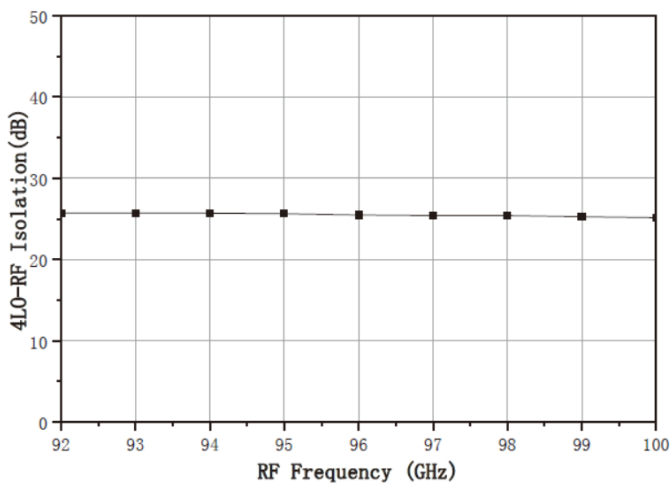
RF Output power vs.IF input power@Freq_IF=97GHz



Conversion gain vs. Freq



4LO-RF Isolation vs. Freq



Tips:

- 1) Good grounding and heat dissipation are required during use. MoCu with thermal expansion coefficient close to InP substrate ($4.6 \times 10^{-6}/K$) is recommended as carrier.
- 2) The chips are electrostatic sensitive devices. Anti-static devices should be paid attention to during use, transportation and operation, and severe collisions and drops should be avoided to avoid damaging the product.
- 3) It is recommended to install decoupling capacitors according to the recommended assembly drawing when using;
- 4) It is recommended to use the diameter of 25um gold wire as feed, input and output interconnection of chips;
- 5) This chip is a hydrogen sensitive device with a hydrogen resistance of 2000 ppm. It is recommended to control the hydrogen concentration in the sealed chamber when using.